

EVVOSEMI[®]

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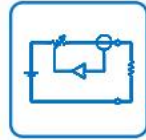
ESD



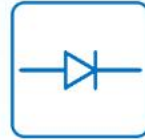
TVS



MOS



LDO



Diode



Sensor



DC-DC

Product Specification

▶ Domestic	Part Number	NJW21193G
▶ Overseas	Part Number	NJW21193G
▶ Equivalent	Part Number	NJW21193G

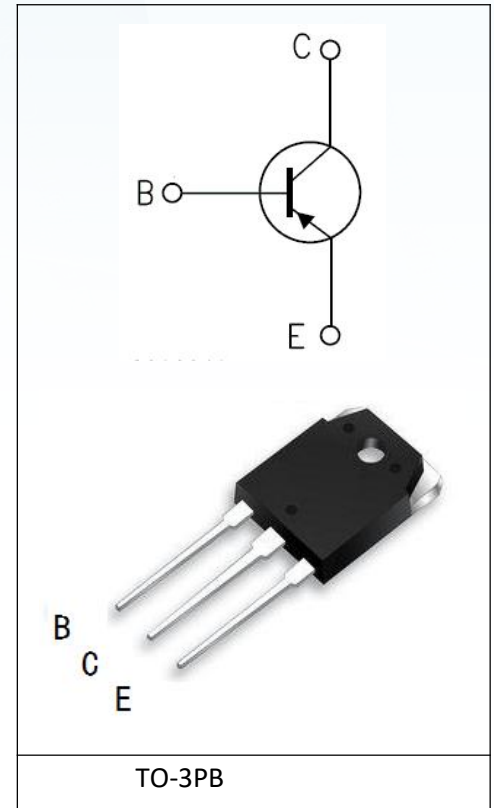
EV is the abbreviation of name EVVO

Transistor Silicon PNP Epitaxial Type

Power Amplifier Applications

- Complementary to NJW21194G
- High collector voltage: $V_{CEO} = -250V$ (min)
- Recommended for 100-W high-fidelity audio frequency amplifier Output stage

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



Absolute Maximum Ratings($T_c=25^{\circ}C$):

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-400	V
Collector-emitter voltage	V_{CEO}	-250	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current	I_C	-16	A
Base current	I_B	-5	A
Collector power dissipation ($T_c=25^{\circ}C$)	P_C	200	W
Junction temperature	T_j	150	$^{\circ}C$
Storage temperature range	T_{STG}	-55~150	$^{\circ}C$

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Electrical Characteristics (Tc=25°C):

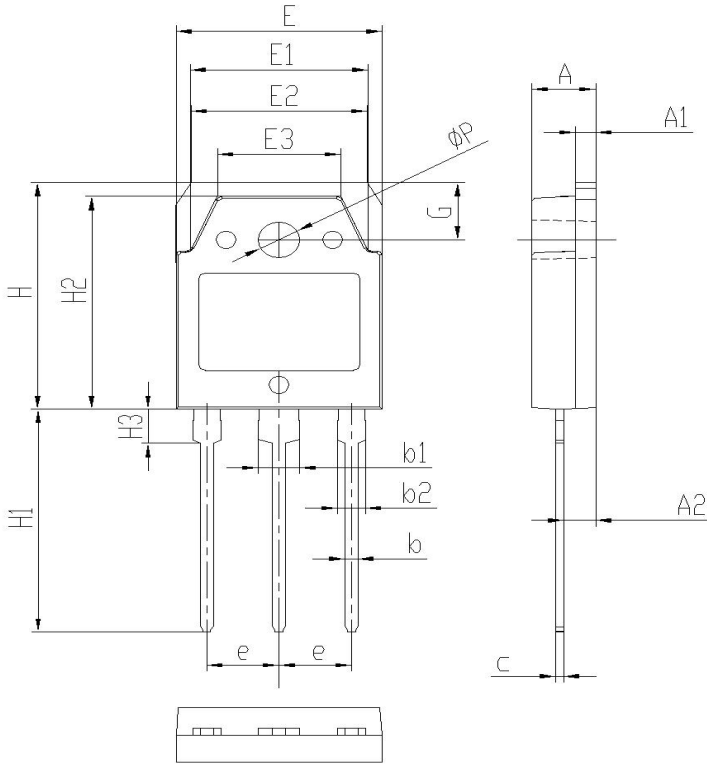
Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} =-250V; I _E =0			-10.0	uA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V; I _C =0			-10.0	uA
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-50mA; I _B =0	-250			V
DC current gain	h _{FE}	V _{CE} =-5V; I _C =-8A;	20		80	
	h _{FE(2)}	V _{CE} =-5V; I _C =-16A;	8			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-8A; I _B =-0.8A			-1.4	V
	V _{CE(sat)}	I _C =-16A; I _B =-3.2A			-4	V
Base-emitter voltage	V _{BE}	V _{CE} =-5V; I _C =-8A			-2.2	V
Transition frequency	f _T	V _{CE} =-10V; I _C =-1A	4			MHz

Symbol	Paramter	Typ	Units
R _{θJC}	Junction-to-Case	0.63	°C/W

Transistor Silicon PNP Epitaxial Type

Package Information

TO-3PB PACKAGE



Symbol	UNIT(mm)		
	Min.	Typ.	Max.
A	4.60	4.80	5.00
A1	1.3	1.5	1.7
A2	2.20	2.40	2.60
b	0.80	1.0	1.20
b1	2.90	3.10	3.30
b2	1.80	2.00	2.20
c	0.50	0.60	0.70
e	5.25	5.45	5.65
E	15.2	15.6	16.0
E1	13.2	13.4	13.6
E2	15.1	15.3	16.5
E3	9.1	9.3	9.5
H	19.8	20.0	20.2
H1	19.0	19.5	20.0
H2	18.3	18.5	18.7
H3	2.8	3.0	3.2
G	4.8	5.0	5.2
ΦP	3.00	3.20	3.40

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